



**THE DATASHEET OF
TC74LCX540FT(EL,M)**



SMPS MOSFET

IRF7457PbF

HEXFET® Power MOSFET

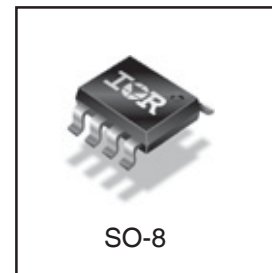
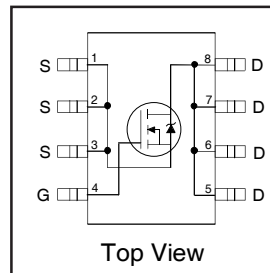
Applications

- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

V_{DSS}	R_{DS(on)} max	I_D
20V	7.0mΩ	15A

Benefits

- Ultra-Low R_{DS(on)}
- Very Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-to-Source Voltage	± 20	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	15	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	12	
I _{DM}	Pulsed Drain Current ^①	120	
P _D @ T _A = 25°C	Maximum Power Dissipation ^③	2.5	W
P _D @ T _A = 70°C	Maximum Power Dissipation ^③	1.6	W
	Linear Derating Factor	0.02	W/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJL}	Junction-to-Drain Lead	—	20	°C/W
R _{θJA}	Junction-to-Ambient ^④	—	50	

Notes ① through ④ are on page 8
www.irf.com

IRF7457PbF

International
IR Rectifier

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.023	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	5.5	7.0	mΩ	V _{GS} = 10V, I _D = 15A ③
		—	8.0	10.5		V _{GS} = 4.5V, I _D = 12A ③
V _{GS(th)}	Gate Threshold Voltage	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 16V, V _{GS} = 0V
		—	—	100		V _{DS} = 16V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -16V

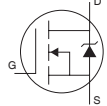
Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	30	—	—	S	V _{DS} = 16V, I _D = 12A
Q _g	Total Gate Charge	—	28	42	nC	I _D = 12A
Q _{gs}	Gate-to-Source Charge	—	11	17		V _{DS} = 10V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	10	15		V _{GS} = 4.5V, ③
Q _{oss}	Output Gate Charge	—	25	38		V _{GS} = 0V, V _{DS} = 10V
t _{d(on)}	Turn-On Delay Time	—	14	—	ns	V _{DD} = 10V,
t _r	Rise Time	—	16	—		I _D = 12A
t _{d(off)}	Turn-Off Delay Time	—	16	—		R _G = 1.8Ω
t _f	Fall Time	—	7.5	—		V _{GS} = 4.5V ③
C _{iss}	Input Capacitance	—	3100	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1600	—		V _{DS} = 10V
C _{rss}	Reverse Transfer Capacitance	—	270	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	265	mJ
I _{AR}	Avalanche Current①	—	15	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	120		
V _{SD}	Diode Forward Voltage	—	0.8	1.3	V	T _J = 25°C, I _S = 12A, V _{GS} = 0V ③
		—	0.67	—		T _J = 125°C, I _S = 12A, V _{GS} = 0V
t _{rr}	Reverse Recovery Time	—	50	75	ns	T _J = 25°C, I _F = 12A, V _R = 15V
Q _{rr}	Reverse Recovery Charge	—	70	105		di/dt = 100A/μs ③
t _{rr}	Reverse Recovery Time	—	50	75	ns	T _J = 125°C, I _F = 12A, V _R = 15V
Q _{rr}	Reverse Recovery Charge	—	74	110		di/dt = 100A/μs ③

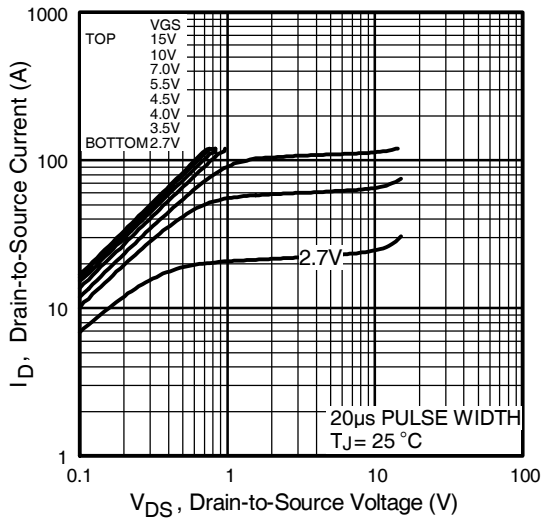


Fig 1. Typical Output Characteristics

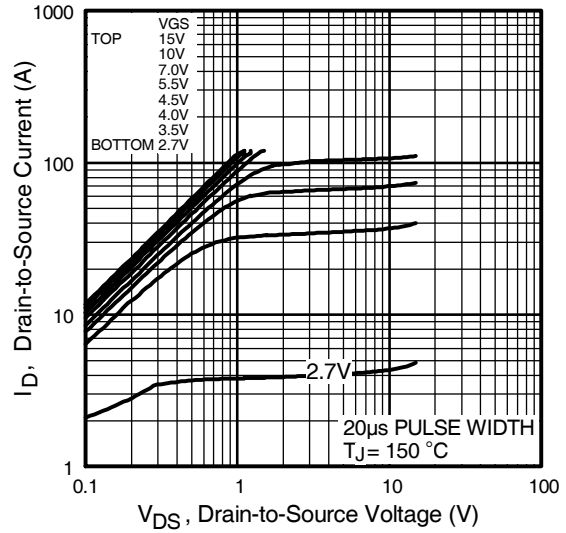


Fig 2. Typical Output Characteristics

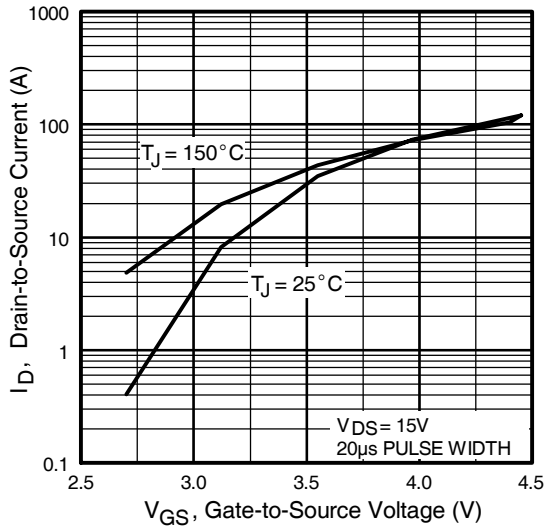


Fig 3. Typical Transfer Characteristics

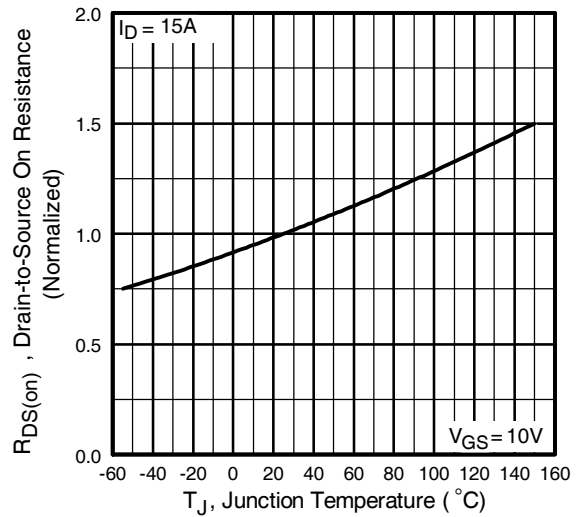


Fig 4. Normalized On-Resistance Vs. Temperature

IRF7457PbF

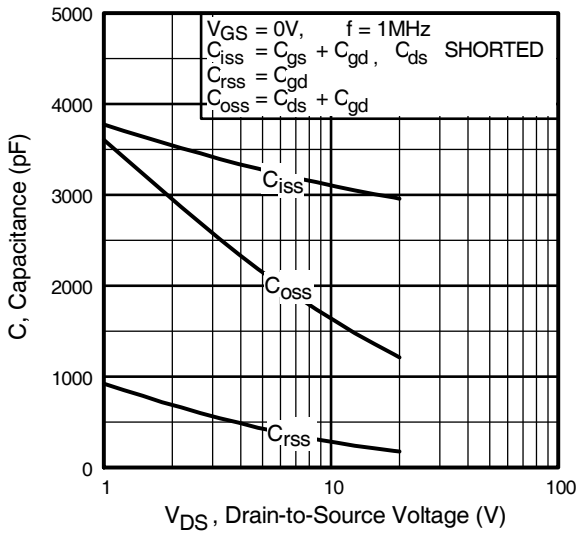


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

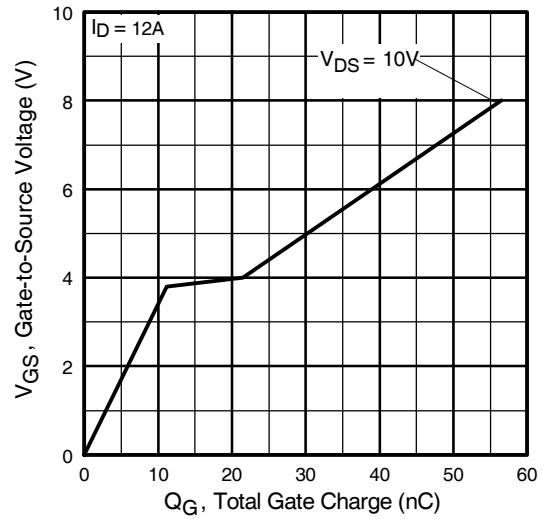


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

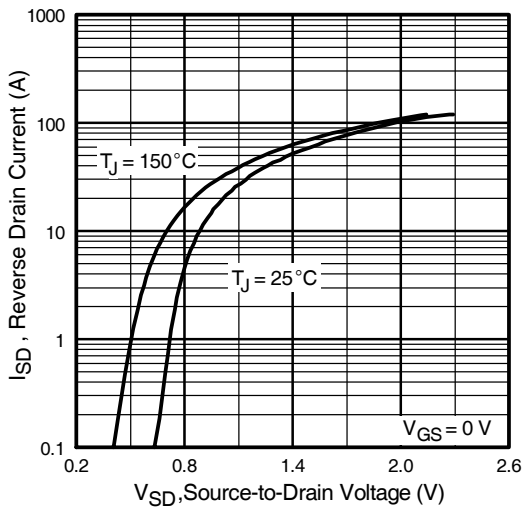


Fig 7. Typical Source-Drain Diode Forward Voltage

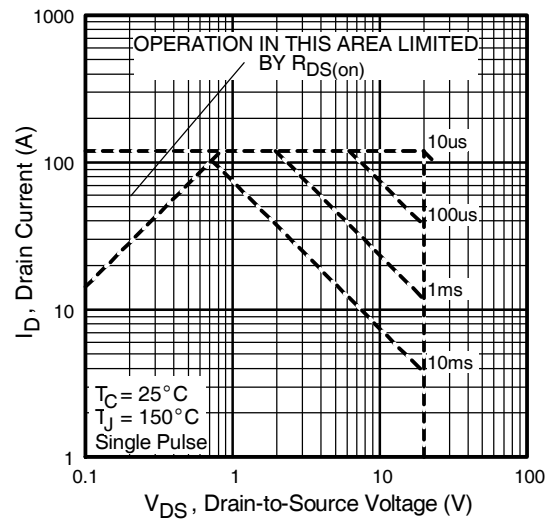


Fig 8. Maximum Safe Operating Area

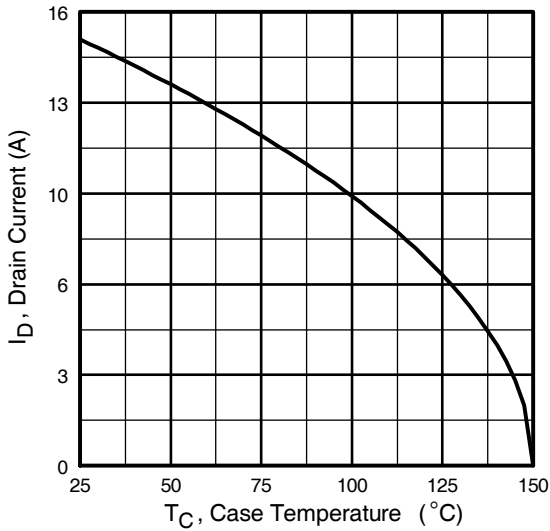


Fig 9. Maximum Drain Current Vs. Case Temperature

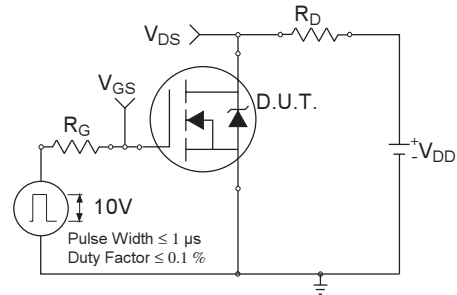


Fig 10a. Switching Time Test Circuit

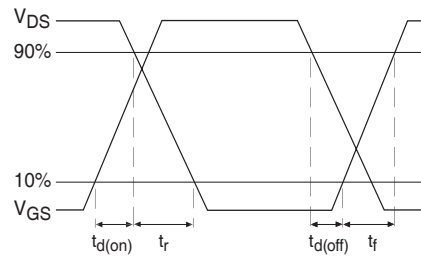


Fig 10b. Switching Time Waveforms

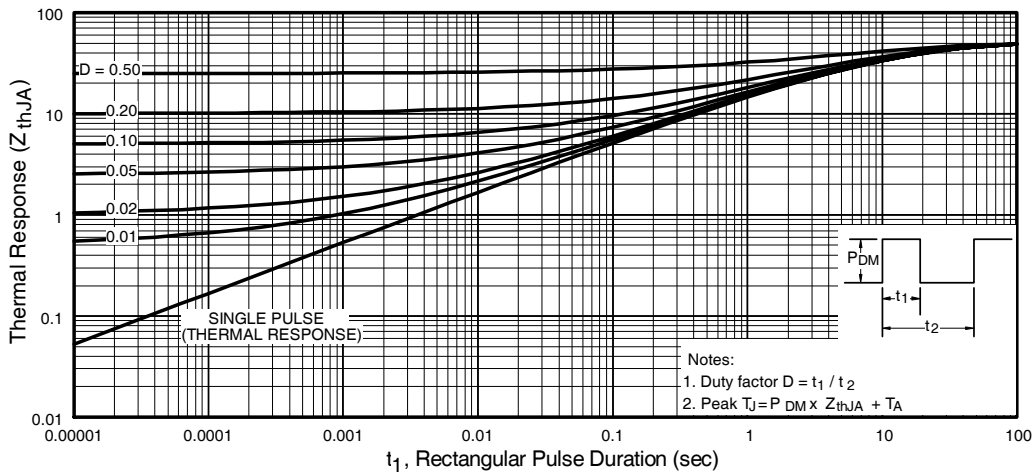


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRF7457PbF

International
IR Rectifier

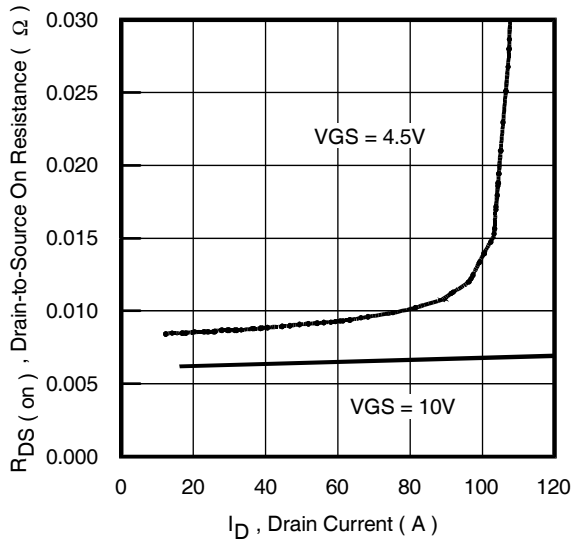


Fig 12. On-Resistance Vs. Drain Current

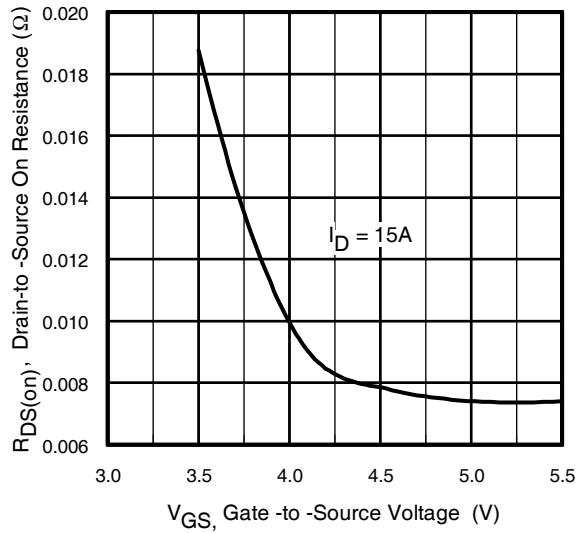


Fig 14. On-Resistance Vs. Gate Voltage

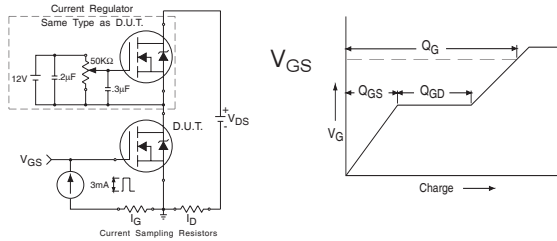


Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

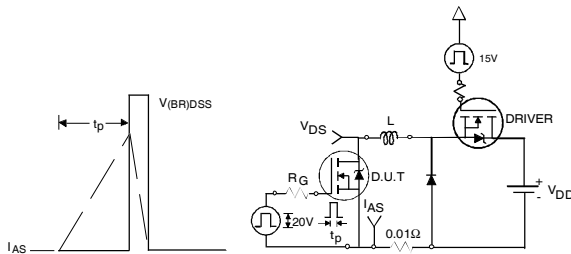


Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

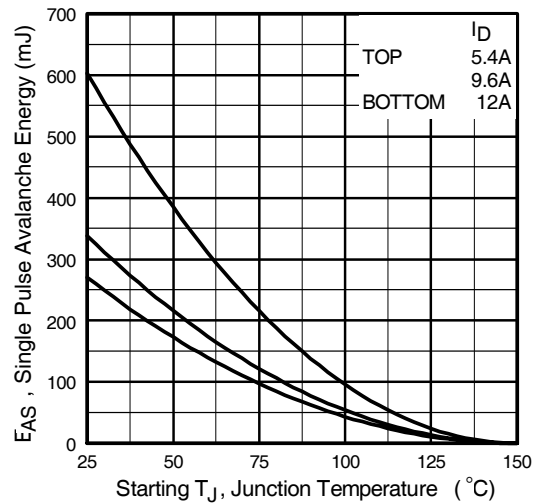
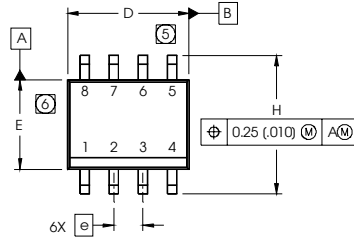


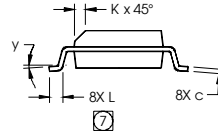
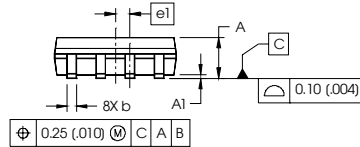
Fig 14c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Outline

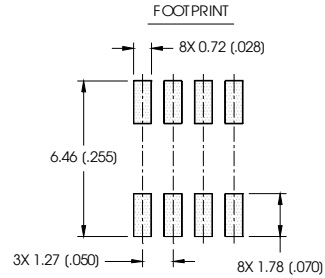
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

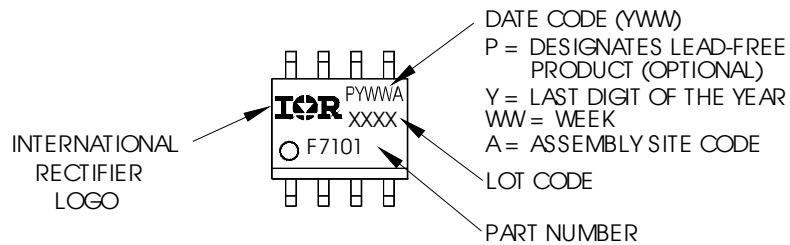


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
 5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
 6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
 7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking Information (Lead-Free)

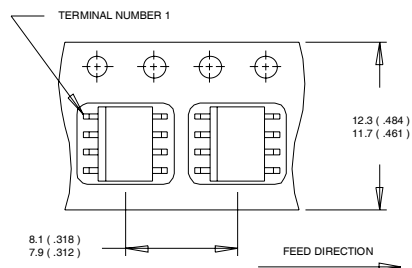
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



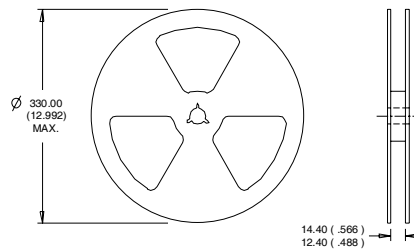
IRF7457PbF

International
IR Rectifier

SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 3.7\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 12\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10\text{ sec}$

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 10/04

www.irf.com

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- [View TC74LCX540FT\(EL,M\) on WIN SOURCE](#)
- [Toshiba Semiconductor and Storage Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management